High Current LED Driver

This device is designed to replace discrete solutions for driving LEDs in low voltage AC–DC applications 5.0 V, 12 V or 24 V. An external resistor allows the circuit designer to set the drive current for different LED arrays. This discrete integration technology eliminates individual components by combining them into a single package, which results in a significant reduction of both system cost and board space. The device is a small surface mount package (SO–8).

Features

- Supplies Constant LED Current for Varying Input Voltages
- External Resistor Allows Designer to Set Current up to 500 mA
- Offered in Surface Mount Package Technology (SO-8)
- AEC-Q101 Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- Pb-Free Package is Available

Benefits

- Maintains a Constant Light Output During Battery Drain
- One Device can be used for Many Different LED Products
- Reduces Board Space and Component Count
- Simplifies Circuit and System Designs

Typical Applications

- Portables: For Battery Back–up Applications, also Simple Ni–CAD Battery Charging
- Industrial: Low Voltage Lighting Applications and Small Appliances
- Automotive: Tail Lights, Directional Lights, Back-up Light, Dome Light

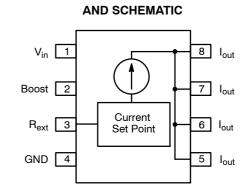
Pin	Symbol	Description
1	V _{in}	Positive input voltage to the device
2	Boost	This pin may be used to drive an external transistor as described in the App Note AND8198/D.
3	R _{ext}	An external resistor between R_{ext} and V_{in} pins sets different current levels for different application needs
4	GND	Ground
5, 6, 7, 8	l _{out}	The LEDs are connected from these pins to ground



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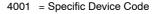
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PIN CONFIGURATION



MARKING DIAGRAM





- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping [†]
NUD4001DR2	SO-8	2500 / Tape & Reel
NUD4001DR2G	SO-8 (Pb-Free)	2500 / Tape & Reel
NSVD4001DR2G	SO-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS (T_A = 25° C unless otherwise noted)

Rating	Symbol	Value	Unit
Continuous Input Voltage	V _{in}	30	V
Non-repetitive Peak Input Voltage (t \leq 1.0 ms)	V _p	60	V
Output Current (For $V_{drop} \le 2.2 \text{ V}$) (Note 1)	l _{out}	500	mA
Output Voltage	V _{out}	28	V
Human Body Model (HBM)	ESD	1000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. $V_{drop} = V_{in} - 0.7 V - V_{LEDs}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Operating Ambient Temperature	T _A	-40 to +125	°C
Maximum Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Total Power Dissipation (Note 2) Derating above 25°C (Figure 3)	PD	1.13 9.0	W mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	110	°C/W
Thermal Resistance, Junction-to-Lead (Note 2)	$R_{ hetaJL}$	77	°C/W

2. Mounted on FR-4 board, 2 in sq pad, 2 oz coverage.

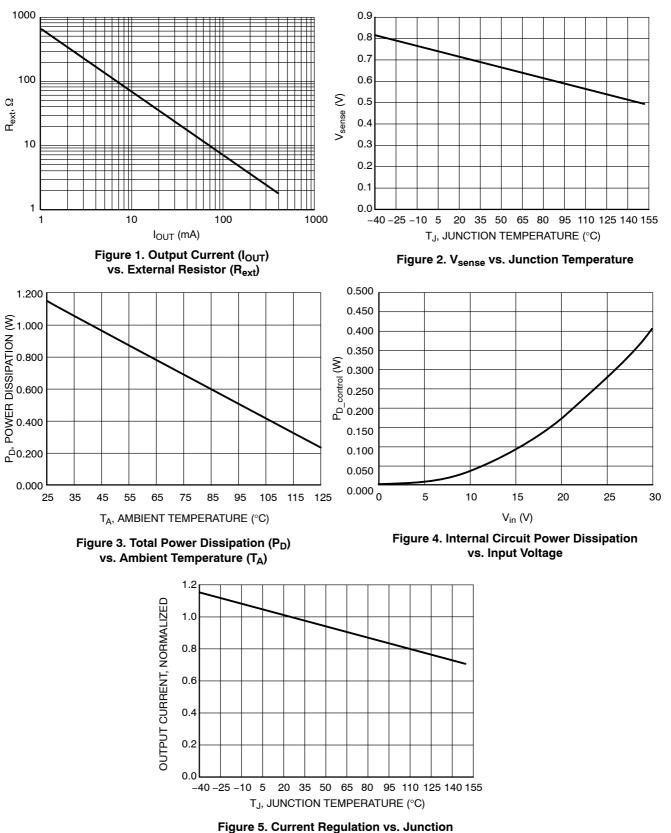
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Current1 $(V_{in} = 12 \text{ V}, \text{ R}_{ext} = 2.0 \Omega, \text{ V}_{LEDs} = 10 \text{ V})$	I _{out1}	305	325	345	mA
Output Current2 $(V_{in} = 30 \text{ V}, \text{ R}_{ext} = 7.0 \Omega, \text{ V}_{LEDs} = 24 \text{ V})$	I _{out2}	95	105	115	mA
Bias Current (V _{in} = 12 V, R _{ext} = Open, V _{LEDs} = 10 V)	I _{Bias}	_	5.0	8.0	mA
Voltage Overhead (Note 3)	V _{over}	1.4	-	-	V

3. $V_{over} = V_{in} - V_{LEDs}$.

TYPICAL PERFORMANCE CURVES

(T_A = 25°C unless otherwise noted)

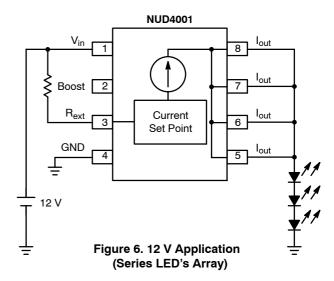


Temperature

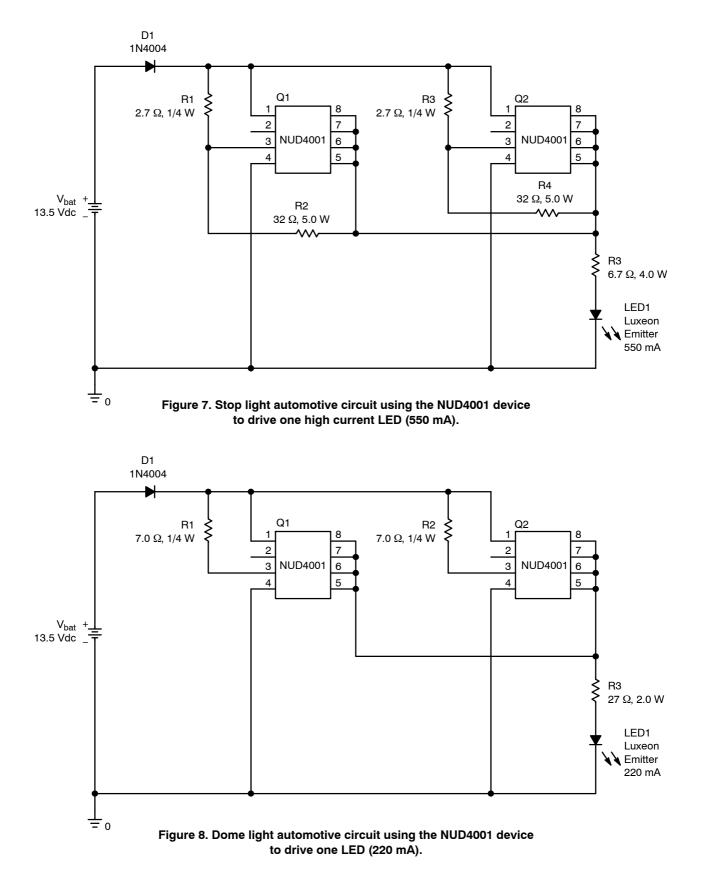
APPLICATION INFORMATION

Design Guide

- 1. Define LED's current: a. $I_{LED} = 350 \text{ mA}$
- 2. Calculate Resistor Value for R_{ext} : a. $R_{ext} = V_{sense}$ (see Figure 2) / I_{LED} b. $R_{ext} = 0.7$ ($T_J = 25$ °C)/ $0.350 = 2.0 \Omega$
- 3. Define V_{in}: a. Per example in Figure 6, V_{in} = 12 V
- 4. Define V_{LED} @ I_{LED} per LED supplier's data sheet:
 - a. Per example in Figure 6, $V_{LED} = 3.5 \text{ V} + 3.5 \text{ V} + 3.5 \text{ V} = 10.5 \text{ V}$
- 5. Calculate V_{drop} across the NUD4001 device: a. $V_{drop} = V_{in} - V_{sense} - V_{LED}$
 - b. $V_{drop} = 12 \text{ V} 0.7 \text{ V} (T_J = 25 \text{ °C}) 10.5 \text{ V}$
 - c. $V_{drop} = 0.8 V$
- 6. Calculate Power Dissipation on the NUD4001 device's driver:
 a. P_{D_driver} = V_{drop} * I_{out}
 b. P_{D_driver} = 0.8 V x 0.350 A
 - $c_{\text{PD}} = 0.280 \text{ Watts}$
 - c. $P_{D_{driver}} = 0.280$ Watts
- 7. Establish Power Dissipation on the NUD4001 device's control circuit per Figure 4:
 a. P_{D_control} = Figure 4, for 12 V input voltage
 b. P_{D_control} = 0.055 W
- 8. Calculate Total Power Dissipation on the device:
 a. P_{D_total} = P_{D_driver} + P_{D_control}
 b. P_{D total} = 0.280 W + 0.055 W = 0.335 W
- 9. If P_{D_total} > 1.13 W (or derated value per Figure 3), then select the most appropriate recourse and repeat steps 1 through 8:
 a. Reduce V_{in}
 - b. Reconfigure LED array to reduce V_{drop}
 - c. Reduce I_{out} by increasing R_{ext}
 - d. Use external resistors or parallel device's configuration (see application note AND8156)
- Calculate the junction temperaure using the thermal information on Page 7 and refer to Figure 5 to check the output current drop due to the calculated junction temperature. If desired, compensate it by adjusting the value of R_{ext}.



TYPICAL APPLICATION CIRCUITS



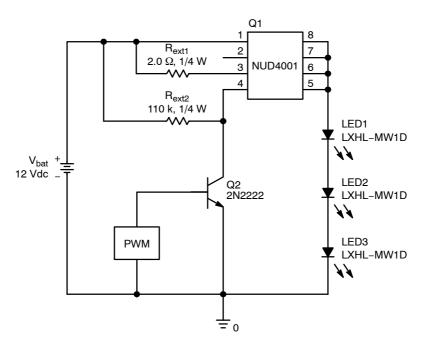


Figure 9. NUD4001 Device Configuration for PWM

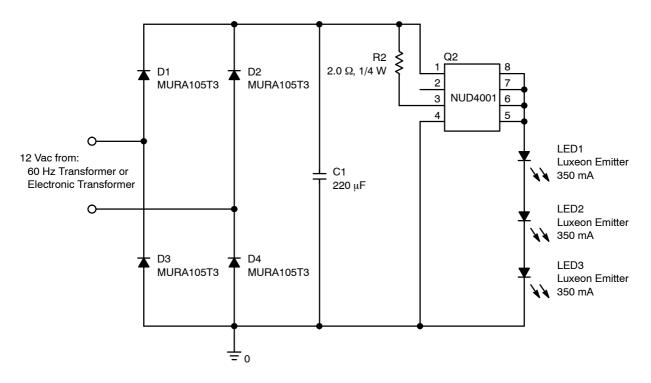


Figure 10. 12 Vac landscape lighting application circuit using the NUD4001 device to drive three 350 mA LEDs.

THERMAL INFORMATION

NUD4001, NSVD4001 Power Dissipation

The power dissipation of the SO–8 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the SO–8 package, P_D can be calculated as follows:

$$P_{D} = \frac{T_{Jmax} - T_{A}}{R_{\theta}JA}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 1.13 W.

$$P_D = \frac{150^\circ C - 25^\circ C}{110^\circ C} = 1.13 W$$

The 110° C/W for the SO–8 package assumes the use of a FR–4 copper board with an area of 2 square inches with 2 oz coverage to achieve a power dissipation of 1.13 W. There are other alternatives to achieving higher dissipation from the SOIC package. One of them is to increase the copper area to

reduce the thermal resistance. Figure 11 shows how the thermal resistance changes for different copper areas. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad®. Using a board material such as Thermal Clad or an aluminum core board, the power dissipation can be even doubled using the same footprint.

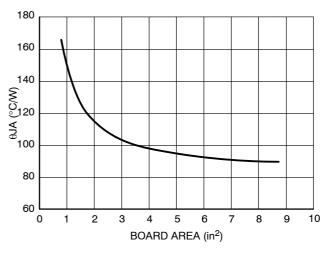


Figure 11. 0JA versus Board Area

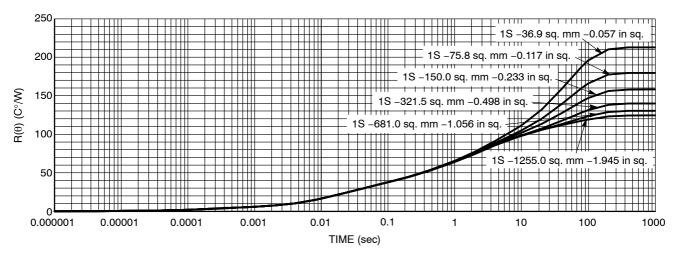


Figure 12. Transient Thermal Response

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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